CRMCP18N20B

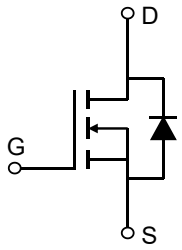
N-Channel 200V,132mΩ Typ. Power MOSFET

Description

Features

- 200V, 18A

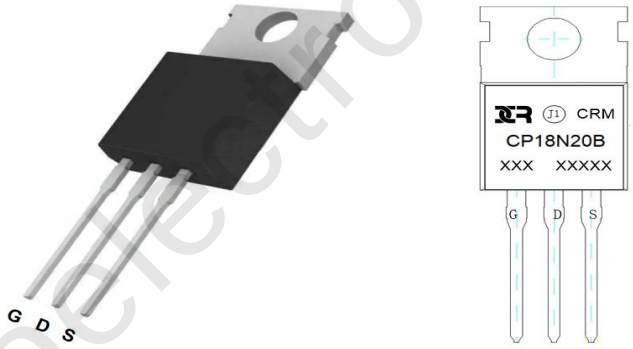
  $R_{DS(ON)}$ Typ =132mΩ @ V_{GS} = 10V
- Fast Switching
- Improved dv/dt Capability
- 100% UIS TESTED!
- 100% ΔVds TESTED!



Schematic Diagram

Application

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	TUBE(pcs)	Inner Box (pcs)	Per Carton (pcs)
CRMCP18N20B	CRMCP18N20B	TO-220C-3L	TUBE	50	2000	8000

Absolute Maximum Ratings (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		200	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	18	A
		T_C = 100°C	10.8	A
I_{DM}	Pulsed Drain Current (1)		72	A
E_{AS}	Single Pulsed Avalanche Energy (2)		169	mJ
P_D	Power Dissipation	T_C = 25°C	150	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.83	°C/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	200	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 200V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2	3	4	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS} = 10V, I_D = 9A	-	132	172	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz	-	911	-	pF
C_{oss}	Output Capacitance		-	165	-	pF
C_{rss}	Reverse Transfer Capacitance		-	87	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, V_{DS} = 160V, I_D =18A	-	60	-	nC
Q_{gs}	Gate Source Charge		-	4	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	37	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 100V, I_D= 18A, R_{GEN} = 5Ω	-	12	-	ns
t_r	Turn-On Rise Time		-	145	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	50	-	ns
t_f	Turn-Off Fall Time		-	15	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	18	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	72	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S = 9A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 18A, di/dt = 100A/us	-	200	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	1.2	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=26A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Test Circuit

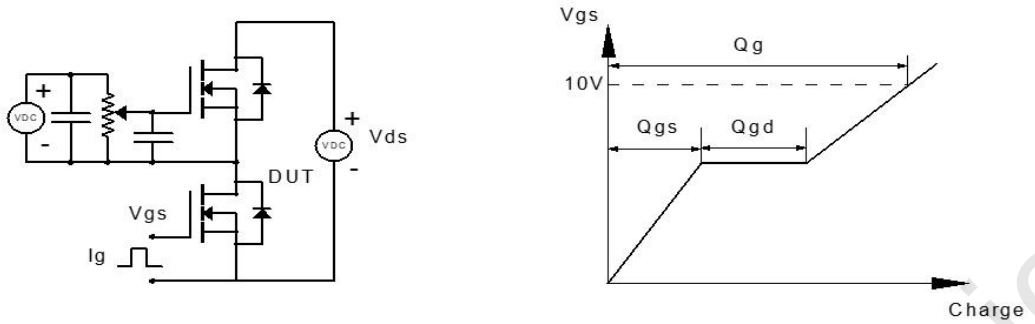


Figure 1: Gate Charge Test Circuit & Waveform

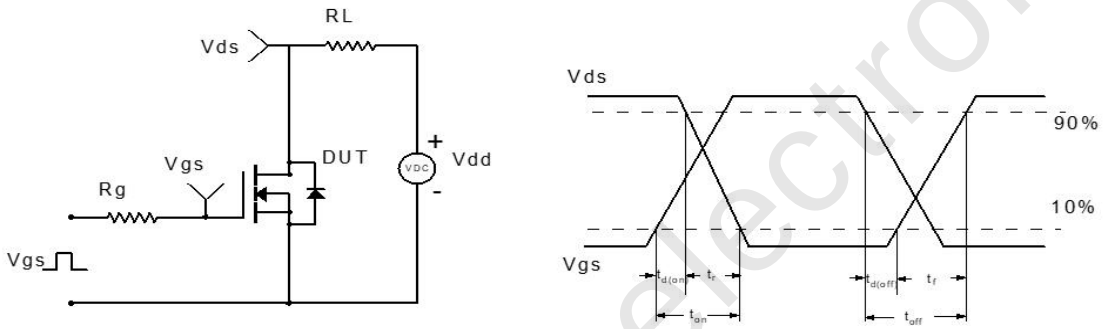


Figure 2: Resistive Switching Test Circuit & Waveform

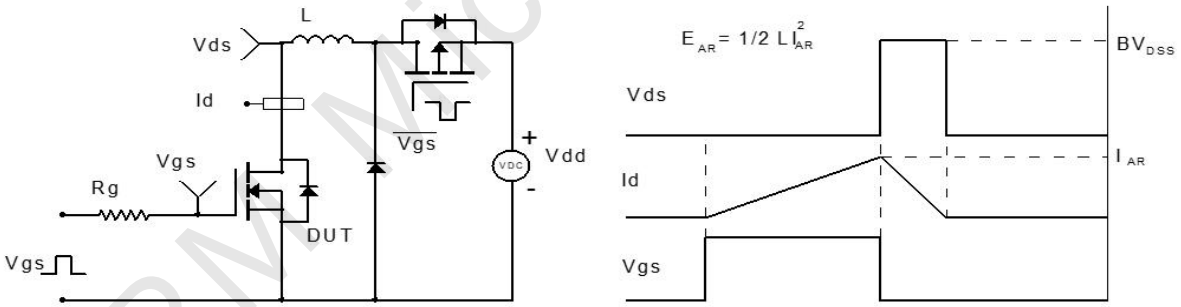


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

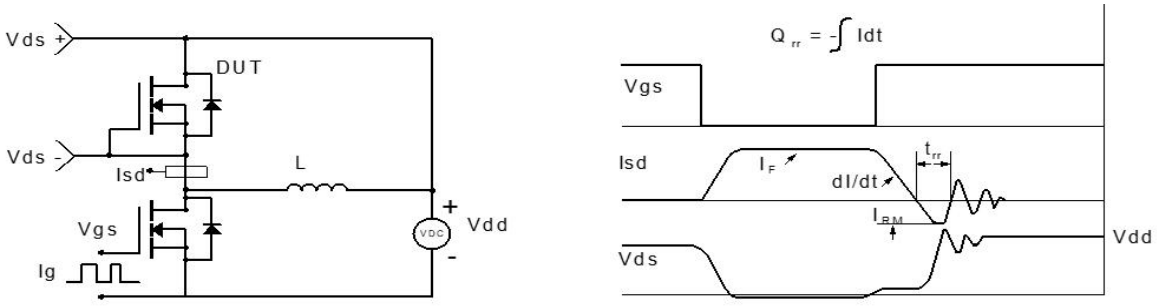
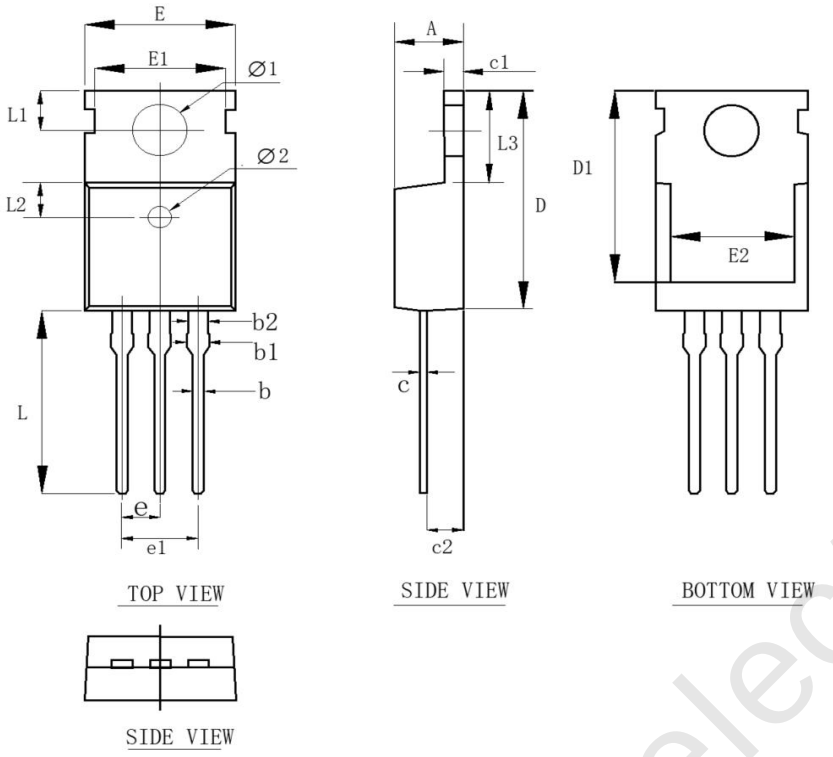


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(TO-220C-3L)



COMMON DIMENSIONS (UNITS OF MEASURE=mm)			
SYMBOL	MIN	NOM	MAX
A	4.30	4.50	4.70
b	0.70	0.80	0.90
b1	——	——	1.42
b2	1.17	1.27	1.37
c	0.40	0.50	0.60
c1	1.25	1.30	1.35
c2	2.20	2.40	2.60
D	15.45	15.65	15.85
D1	13.20	13.40	13.60
E	9.80	10.00	10.20
E1	8.60	8.70	8.80
E2	7.80	8.00	8.20
e1	4.88	5.08	5.28
L	12.95	13.15	13.35
L1	2.70	2.80	2.90
L2	2.40	2.50	2.60
L3	6.30	6.50	6.70
Ø1	3.50	3.60	3.70
Ø2	1.35	1.50	1.65
e	2.54BSC		

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